

Kindly replace the Abstract with the following amended Abstract:

A' A method of fabricating a semiconductor device having a recess region in an insulation layer on a silicon substrate, comprising the steps of depositing a barrier metal over the entire surface of the insulation layer including the substrate surface in the recess region, depositing selectively an anti-nucleation layer on the barrier metal except in the recess region, depositing a CVD-Al layer on the barrier metal in the recess region, depositing a metal or a metal alloy inhibiting aluminum migration on the anti-nucleation layer and the barrier metal except in the recess region, and depositing a PVD-Al layer and re-flowing the PVD-Al layer, for improving the quality of aluminum grooves. The present method inhibits PVD-Al migration and grain growth, which results in preventing abnormal patterning in the semiconductor device.

The changes in the Abstract are indicated by brackets for deletions and underlining for insertions.

A method of fabricating a semiconductor device having a recess region in an insulation layer on a silicon substrate, comprising the steps of depositing a barrier metal over the entire surface of the insulation layer including the substrate surface in the recess region, depositing selectively an anti-nucleation layer on the barrier metal except in the recess region, depositing a CVD-Al layer on the barrier metal in the recess region, depositing a metal or a metal alloy inhibiting aluminum migration on the anti-nucleation layer and the barrier metal except in the recess region, and depositing a PVD-Al layer and re-flowing the PVD-Al layer, for improving the quality of aluminum grooves [over those generated using conventional PMD-Al processes]. The present method inhibits PVD-Al migration and grain growth, which results in preventing abnormal patterning in the semiconductor device.